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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/614,354	07/07/2003	Thomas J. Sonderman	2000.100800	7900
7590	07/12/2004			
J. Mike Amerson Williams, Morgan & Amerson, P.C. 10333 Richmond, Suite 1100 Houston, TX 77042				
			EXAMINER NGUYEN, KHIEM D	
			ART UNIT 2823	PAPER NUMBER

DATE MAILED: 07/12/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/614,354

Applicant(s)

THOMAS J. SONDERMAN

Examiner

Khiem D Nguyen

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 07 July 2003.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-22 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-22 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 07 July 2003 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____.
- 4) ☐ Interview Summary (PTO-413) Paper No(s). _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

Claim Objections

Claim 1 is objected to because of the following informalities: In claim 1, line 5, after “said at”, delete “lest” and insert --least--. Appropriate correction is required.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

1. Claims 1-20 are rejected under 35 U.S.C. 102(e) as being anticipated by Kline (U.S. Pub. 2003/0129775).

In re claims 1, 9, and 16, **Kline** discloses a method, comprising: performing at least one electrical test on at least one semiconductor device (page 2, paragraph [0012]); determining at least one parameter of at least one process operation to be performed to form at least one gate insulation layer on a subsequently formed semiconductor device (i.e., memory device, transistor...) based upon electrical data obtained from the at least one electrical test; and performing the at least one process operation comprised of the determined at least one parameter to form at least one gate insulation layer on the subsequently formed semiconductor device (page 2, paragraphs [0013]-[0014] and **FIGS. 1-11**).

In re claims 2 and 10, **Kline** discloses wherein the semiconductor device is at least one of a flash memory device, an application specific integrated circuit and a microprocessor (page 2, paragraph [0012]).

In re claims 3, 11, and 17, **Kline** discloses wherein performing the at least one electrical test on the at least one semiconductor device comprises performing the at least one electrical test on the at least one semiconductor device to determine at least one of a breakdown voltage, a threshold voltage, a state charge, an interface charge, a trapped charge, a surface charge, a programming cycle time and an erase cycle time (page 2, paragraph [0012]).

In re claim 4, **Kline** discloses wherein the semiconductor device is comprised of at least one transistor that is comprised of a gate insulation layer and a gate electrode positioned above the gate insulation layer (page 1, paragraph [0011]).

In re claims 5 and 12, **Kline** discloses wherein the semiconductor device is comprised of a memory device that is comprised of a gate insulation layer, a floating gate layer positioned above the gate insulation layer, an intermediate insulation layer positioned above the floating gate layer, and a control gate layer positioned above the intermediate insulation layer (page 2, paragraph [0011]).

In re claims 6, 13, and 18, **Kline** discloses wherein the at least one process operation is comprised of at least one of a deposition process and a thermal growth process (page 2, paragraph [0014]).

In re claims 7, 14, and 19, **Kline** discloses wherein at least one parameter is comprised of at least one of a temperature, a pressure, a duration, a process gas flow rate,

a process gas composition, a liquid flow rate, a liquid composition, and a power level setting (page 2, paragraph [0012]).

In re claims 8, 15, and 20, Kline discloses wherein the gate insulation layer is comprised of at least one of silicon dioxide and silicon nitride (page 3, paragraph [0013]).

2. Claim 21 is rejected under 35 U.S.C. 102(e) as being anticipated by Kline (U.S. Pub. 2003/0129775).

In re claim 21, Kline discloses a method, comprising: performing at least one electrical test on at least one memory device to determine a duration of a programming cycle performed on the memory devices (page 2, paragraph [0012]); determining at least one parameter of at least one process operation to be performed to form at least one gate insulation layer on a subsequently formed memory device based upon the determined duration of the programming cycle; and performing the at least one process operation comprised of the determined at least one parameter to form at least one gate insulation layer on the subsequently formed memory device (page 2, paragraphs [0013]-[0014] and FIGS. 1-11).

3. Claim 22 is rejected under 35 U.S.C. 102(e) as being anticipated by Kline (U.S. Pub. 2003/0129775).

In re claim 22, Kline discloses a method, comprising: performing at least one electrical test on at least one memory device to determine a duration of an erase cycle performed on the memory devices (page 2, paragraph [0012]); determining at least one parameter of at least one process operation to be performed to form at least one gate insulation layer on a subsequently formed memory device based upon the determined

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duration of the erase cycle; and performing the at least one process operation comprised of the determined at least one parameter to form at least one gate insulation layer on the subsequently formed memory device (page 2, paragraphs [0013]-[0014] and FIGS. 1-11).

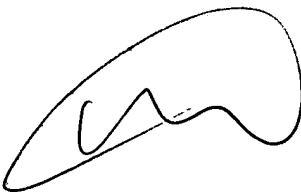
Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khiem D Nguyen whose telephone number is (571) 272-1865. The examiner can normally be reached on Monday-Friday (8:00 AM - 5:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (571) 272-1855. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 305-3432 for regular communications and (703) 305-3432 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

K.N.
July 6, 2004



W. DAVID COLEMAN
PRIMARY EXAMINER